Form PTO 1449 U.S. DEPARTMENT OF COMMERCE ATTY DOCKET NO. SERIAL NO. (Modified) PATENT AND TRADEMARK OFFICE 210295US99 09/897,059 **APPLICANT** LIST OF REFERENCES CITED BY APPLICANT Tomasz L. KLOSOWIAK, et al. FILING DATE **GROUP** July 3, 2001 2814 U.S. PATENT DOCUMENTS **EXAMINER** DOCUMENT DATE NAME CLASS SUB FILING DATE NUMBER **CLASS** IF APPROPRIATE 3,802,967 04/09/74 Ladany et al. AB 4,174,422 11/13/79 Matthews et al. AC 4,404,265 09/13/83 Manasevit ΑD 4,482,906 11/13/84 Hovel et al. ΑE 4,523,211 06/11/85 Morimoto et al. ΑF 4,661,176 04/28/87 Manasevit AG 4,793,872 12/27/88 Meunier et al. ΑН 4,846,926 07/11/89 Kay et al. ΑJ 4,855,249 08/08/89 Akasaki et al. ΑI 4,891,091 01/02/90 Shastry ΑK 4,912,087 03/27/90 Aslam et al. AL 4,928,154 05/22/90 Umeno et al. ΑМ 4,963,949 10/16/90 Wanlass et al. ΑN 5,141,894 08/25/92 Bisaro et al. ΑO 5,159,413 10/27/92 Calviello et al. AΡ 5,173,474 12/22/92 Connell et al. ΑQ 5,221,367 06/22/93 Chisholm et al. AR 5,225,031 07/06/93 McKee et al. AS 5,358,925 10/25/94 Neville Connell et al. ¢ AΤ 5,393,352 02/28/95 Summerfelt ΑU 5,418,216 05/23/95 Fork ĀΫ 5,450,812 09/19/95 McKee et al. ΑW 5,478,653 12/26/95 Guenzer ΑX 5,482,003 01/09/96 McKee et al. ΑY 5,514,484 05/07/96 Nashimoto (ΑZ 5,556,463 09/17/96 Guenzer ΒA 5,588,995 12/31/96 Sheldon ВВ 5,670,798 09/23/97 Schetzina BC 5,733,641 03/31/98 Fork et al. BD 5,735,949 04/07/98 Mantl et al. ΒE 5,741,724 04/21/98 Ramdani et al. BF 5,810,923 09/22/98 Yano et al. BG 5,830,270 11/03/98 McKee et al. BH 5,912,068 06/15/99 Jia ВΙ 6,020,222 02/01/00 Wollesen BJ6,045,626 04/04/00 Yano et al. ВK 6,064,078 05/16/00 Northrup et al. BL 6,064,092 05/16/00 Park ВМ 6,096,584 08/01/00 Ellis-Monaghan et al. BN 6,103,008 08/15/00 McKee et al. BO 6,136,666 10/24/00 So BP 6,174,755 01/16/01 Manning ΒQ 6,180,486 01/30/01 eobandung et al.

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INITIAL		DOCUMENT NUMBER	_ L	NAME	CLASS	CLASS	IF APPROPRIATE
1 Duc	CA	3,766,370	10/16/73	Walther			
7	СВ	4,006,989	02/08/77	Andringa			
7	СС	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
$\overline{}$	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	СН	4,999,842	03/12/91	Huang et al.			
	СІ	5,081,062	01/14/92	Vasudev et al.			
	Cl	5,155,658	10/13/92	Inam et al.			
-	ск	5,248,564	09/28/93	Ramesh			Tana
	CL	5,260,394	11/09/93	Tazaki et al.	-		
1	СМ	5,270,298	12/14/93	Ramesh			
_	CN	5,286,985	02/15/94	Taddiken			
 	co	5,310,707	05/10/94	Oishi et al.			
-/	СР	5,326,721	07/05/94	Summerfelt			
+-	cq	5,404,581	04/04/95	Honjo			
+	CR	5,418,389	05/23/95	Watanabe		-	
	cs	5,436,759	07/25/95	Dijaii et al.	-		
+	СТ	5,576,879	11/19/96	Nashimoto			
$\overline{}$	CU	5,606,184	02/25/97	Abrokwah, et al.	-	-	<u>, </u>
	cv	5,640,267	06/17/97	May et al.			
+	cw	5,674,366	10/07/97	Hayashi et al.	<u> </u>		
	сх	5,729,641	03/17/98	Chandonnet et al.	_	-	
	CY	5,790,583	08/04/98	Ho			
	cz	5,825,799	10/20/98	Ho et al.			
$\overline{}$	DA	5,857,049	01/05/99	Beranek et al.			=
$\overline{}$	DB	5,874,860	02/23/99	Brunel et al.	- -		
	DC	5,926,496	07/20/99	Ho et al.	-		
	DD	5,937,285	08/10/99	Abrokwah, et al.			-
-	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba	 		-
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem		 	
	DI	6,055,179	04/25/00	Koganei et al.	-	 	
	DJ DJ	6,107,653	08/22/00	Fitzgerald			-
-+-	DK	6,113,690	09/05/00	Yu et al.		-	
	DL	6,114,996	09/05/00	Nghiem			<u> </u>
-+-	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns	_	-	
	DO	6,143,072	11/07/00	McKee et al.		 	
	DP	6,184,144	02/06/01	Lo		 	
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7	DQ	6,222,654	04/24/01	Frigo			

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ATTY DOCKET NO. 210295US99

SERIAL NO. 09/897,059

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	EC	4,876,219	10/24/8				
	ED	4,963,508	10/16/90				
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+	EF	5,063,166	11/05/91	The strain, et al.			
	EG	5,116,461	05/26/92				
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$\overline{}$		5,144,409	06/30/92	- 5.0000 Ct al.			
		5,293,050	09/01/92				
			03/08/94	Chapple-Sokol et al			
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/		5,391,515	02/21/95	Kao et al.			
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1		5,480,829	01/02/96	Abrokwah, et al.			
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E	EQ 5	5,614,739	03/25/97	Abrokwah et al.			
E	R 5	5,729,394	03/17/98	Sevier et al.			
E	S 5	,731,220	03/24/98	Tsu et al.			
E	T 5	,764,676	06/09/98	Paoli et al.			
E	U 5	,777,762	07/07/98	Yamamoto			
E	V 5	,778,018	07/07/98	Yoshikawa et al.			
E	W 5.	,778,116	07/07/98	Tomich			
E	X 5,	801,105	09/01/98	Yano et al.			
E	Y 5,	828,080	10/27/98	Yano et al.			
E		858,814	01/12/99				
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-/		883,996	03/16/99	Ortel			v.,
FC		995,359		Knapp et al.			
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FH			01/16/01	Conrad			
FI		80,252	01/30/01	Farrell et al.			
		42,595	12/30/0	Lehovec			
FJ		98,342	08/16/83	Pitt et al.			
FK		24,589	01/03/84	Thomas et al.			
FL		376,208	10/24/89	Gustafson et al.		\longrightarrow	
FM		32,422	11/84	McGinn et al.			
FN		57,088		Kramer			
FO	4,77	2,929	09/20/88	Manchester et al.			
FP	4,84	1,775		keda et al.			
) FQ	4,84	5,044		Ariyoshi et al.	1 1		

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_(IB	5,656,382		Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	ΙE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	iн	5,776,621	07/07/98	Nashimoto			
	Ш	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	ΙΚ	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
1	IN	5,801,072	09/01/98	Barber			
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\	IP	5,814,583	09/98	Itozaki et al.			
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/	IR	5,827,755	10/27/98	Yonchara et al.			
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	IU	5,844,260	12/01/98	Ohori			
$\overline{}$	IV	5,846,846	12/08/98	Suh et al.			
-}	lw	5,863,326	01/26/99	Nause et al.		1	`
-/	IX	5,872,493	02/16/99	Ella			C A D
+	IY	5,879,956	03/99	Seon et al.			Company of the compan
-	IZ	5,880,452	03/09/99	Plesko			
-\	JA	5,883,564	03/16/99	Partin			· · · · · · · · · · · · · · · · · · ·
	JB	5,907,792	05/25/99	Droopad et al.			<u> </u>
+-	nc PD	5,937,274	08/10/99	Kondow et al.			
	ND ND	5,948,161	09/07/99	Kizuki			
$\overline{}$	JE JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			· · · · · · · · · · · · · · · · · ·
	JG	5,987,011	11/16/99	Toh			
	JН	6,022,140	02/08/00	Fraden et al.			
	JI JI	6,022,140	02/08/00	Yu et al.		ļ <u>.</u>	
	JJ	6,023,082	02/08/00	McKee et al.			
/_	JΚ	6,028,853	02/22/00	Haartsen			
	JL.	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al			
	ŊΝ	6,088,216	07/00	Laibowitz et al.			
	μO	6,090,659	07/00	Laibowitz et al.			
)	JР	6,107,721	08/22/00	Lakin			

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	кс	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	кн	6,313,486	11/01	Kencke et al.			· · · · · · · · · · · · · · · · · · ·
	KI	6,316,832	11/13/01	Tsuzuki et al.		<u> </u>	
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
1	KL	4,756,007	07/05/88	Qureshi et al.			
	КМ	4,773,063	09/20/88	Hunsperger et al.	- 		
	KN	5,394,489	02/28/95	Koch			
_/	ко	5,406,202	04/11/95	Mehrgardt et al.			
7	KP	5,528,067	06/18/96	Farb et al.			
/	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
/	ΚV	6,252,261	06/26/01	Usui et al.			
	ĸw	6,255,198	07/03/01	Linthicum et al.		- 5	
	кх	6,268,269	07/31/01	Lee et al.			
	KY	6,291,319	09/18/01	Yu et al.			
	KZ	6,316,785	11/13/01	Nunoue et al.		<u></u>	<u> </u>
	LA	6,343,171	01/29/02	Yoshimura et al.		;	
1	LB	4,965,649	10/23/90	Zanio et al.			
7	LC	6,253,649	05/01	Kawahara et al.			ું
	LD	6,211,096	04/01	Allman et al.			
	LE	6,239,449	05/29/01	Fafard et al.			
	LF	2001/0013313	08/16/01	Droopad et al.			
	LG	6,184,044	02/06/01	Sone et al.			
	-H	6,011,646	01/04/00	Mirkarimi et al.			
7		5,227,196	07/13/93	Itoh			
	J	6,150,239	11/21/00	Goesele et al.	+		
1	.K	5,441,577	08/15/95	Sasaki et al.	+		
1	.L	4,459,325		Nozawa et al.			
	.М	4,392,297	07/12/83	Little			
1	N.	4,289,920	09/15/81	Hovel	++		
7	.0	5,281,834		Cambou et al.			
	P.	4,901,133	02/13/90	Curran et al.			
(L	Q E	5,514,904		Onga et al.			

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